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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

Akito KURAMATA et al.

Serial No.: 09/313,764

Group Art Unit: 2823

Filed: May 18, 1999

Examiner: W. Coleman

For: OPTICAL SEMICONDUCTOR DEVICE HAVING AN EPITAXIAL LAYER OF
III-V COMPOUND SEMICONDUCTOR MATERIAL CONTAINING N AS A
GROUP V ELEMENT

PRELIMINARY AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

April 30, 2002

Sir:

Prior to calculation of the filing fee and examination of this application, please amend the above-identified application as follows:

05/01/2002 JADD01	00000028 09313764
02 FC:103	72.00 OP
03 FC:102	420.00 OP

IN THE CLAIMS:

Please amend the claims 1 and 21 as follows:

1. (Amended) An optical semiconductor device, comprising:
 - a substrate of SiC having a first conductivity type;
 - a buffer layer of AlGaN formed on said substrate epitaxially, said buffer layer having said first conductivity type and a composition represented by a compositional parameter x as $Al_xGa_{1-x}N$;
 - a first cladding layer having said first conductivity type, said first cladding layer being formed on said buffer layer epitaxially;
 - an active layer formed epitaxially on said first cladding layer;